

2N4401

MMBT4401





NPN General Pupose Amplifier

This device is designed for use as a medium power amplifier and switch requiring collector currents up to 500 mA.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	40	V
V _{CBO}	Collector-Base Voltage	60	V
V _{EBO}	Emitter-Base Voltage	6.0	V
Ic	Collector Current - Continuous	600	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Characteristic Max		Units
		2N4401	*MMBT4401	
P_D	Total Device Dissipation Derate above 25°C	625 5.0	350 2.8	mW mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	°C/W

^{*}Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

These ratings are based on a maximum junction temperature of 150 degrees C.
 These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

NPN General Purpose Amplifier (continued)

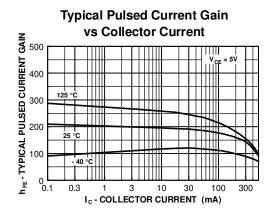
Electrica	l Characteristics	TA = 25°C unless other

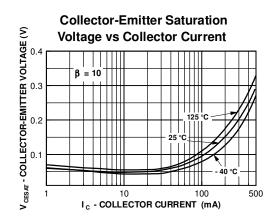
Symbol	Parameter	Test Conditions	Min	Max	Units
Syllibol	Farameter	rest Conditions	IVIIII	IVIAX	Units
OFF CHA	RACTERISTICS				
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 1.0 \text{ mA}, I_B = 0$	40		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_{\rm C} = 0.1 \text{ mA}, I_{\rm E} = 0$	60		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 0.1 \text{ mA}, I_C = 0$	6.0		V
I _{BL}	Base Cutoff Current	$V_{CE} = 35 \text{ V}, V_{EB} = 0.4 \text{ V}$		0.1	μА
I _{CEX}	Collector Cutoff Current	$V_{CE} = 35 \text{ V}, V_{EB} = 0.4 \text{ V}$		0.1	μΑ
	RACTERISTICS*				
h _{FE}	DC Current Gain	I _C = 0.1 mA, V _{CE} = 1.0 V	20		
	Do danon dan	$I_C = 1.0 \text{ mA}, V_{CE} = 1.0 \text{ V}$	40		
		$I_C = 10 \text{ mA}, V_{CE} = 1.0 \text{ V}$	80		
		$I_C = 150 \text{ mA}, V_{CE} = 1.0 \text{ V}$	100	300	
		$I_{\rm C} = 500 \text{ mA}, V_{\rm CE} = 2.0 \text{ V}$	40		
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$ $I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		0.4 0.75	V
	Base-Emitter Saturation Voltage	$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$	0.75	0.95	· ·
V _{BE(sat)}	Dase-Littiller Saluration Voltage		0.75	0.95	V
V _{BE(sat)}	Dase-Emilier Saturation Voltage	$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$	0.75	1.2	V
SMALL S	IGNAL CHARACTERISTICS	I _C = 500 mA, I _B = 50 mA	0.73		V
SMALL S		$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$ $I_C = 20 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 100 \text{ MHz}$	250		V V
SMALL S	IGNAL CHARACTERISTICS	$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$ $I_C = 20 \text{ mA}, V_{CE} = 10 \text{ V},$			MHz
SMALL S	IGNAL CHARACTERISTICS Current Gain - Bandwidth Product	$\begin{split} I_{C} &= 500 \text{ mA}, \ I_{B} = 50 \text{ mA} \\ \\ I_{C} &= 20 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 100 \text{ MHz} \\ \\ V_{CB} &= 5.0 \text{ V}, \ I_{E} = 0, \\ f &= 140 \text{ kHz} \\ \\ V_{BE} &= 0.5 \text{ V}, \ I_{C} = 0, \end{split}$		1.2	
SMALL S f _T C _{cb} C _{eb}	IGNAL CHARACTERISTICS Current Gain - Bandwidth Product Collector-Base Capacitance	$\begin{split} I_C &= 500 \text{ mA}, \ I_B = 50 \text{ mA} \\ \\ I_C &= 20 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 100 \text{ MHz} \\ \\ V_{CB} &= 5.0 \text{ V}, \ I_E = 0, \\ f &= 140 \text{ kHz} \\ \\ V_{BE} &= 0.5 \text{ V}, \ I_C = 0, \\ f &= 140 \text{ kHz} \\ \\ I_C &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \end{split}$		6.5	pF
SMALL S f _T C _{cb} C _{eb}	IGNAL CHARACTERISTICS Current Gain - Bandwidth Product Collector-Base Capacitance Emitter-Base Capacitance	$\begin{split} I_C &= 500 \text{ mA}, \ I_B = 50 \text{ mA} \\ \\ I_C &= 20 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 100 \text{ MHz} \\ \\ V_{CB} &= 5.0 \text{ V}, \ I_E = 0, \\ f &= 140 \text{ kHz} \\ \\ V_{BE} &= 0.5 \text{ V}, \ I_C = 0, \\ f &= 140 \text{ kHz} \\ \\ I_C &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ \\ I_C &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \end{split}$	250	6.5	pF pF
	IGNAL CHARACTERISTICS Current Gain - Bandwidth Product Collector-Base Capacitance Emitter-Base Capacitance Input Impedance	$\begin{split} I_C &= 500 \text{ mA}, \ I_B = 50 \text{ mA} \\ \\ I_C &= 20 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 100 \text{ MHz} \\ \\ V_{CB} &= 5.0 \text{ V}, \ I_E = 0, \\ f &= 140 \text{ kHz} \\ \\ V_{BE} &= 0.5 \text{ V}, \ I_C = 0, \\ f &= 140 \text{ kHz} \\ \\ I_C &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ \\ I_C &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ \\ I_C &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ \\ I_C &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ \\ I_C &= 1.0 \text{ MA}, \ V_{CE} = 10 \text{ V}, \\ \\ I_C &= 1.0 \text{ MA}, \ V_{CE} = 10 \text{ V}, \\ \\ I_C &= 1.0 \text{ MA}, \ V_{CE} = 10 \text{ V}, \\ \\ I_C &= 1.0 \text{ MA}, \ V_{CE} = 10 \text{ V}, \\ \\ I_C &= 1.0 \text{ MA}, \ V_{CE} = 10 \text{ V}, \\ \\ I_C &= 1.0 \text{ MA}, \ V_{CE} = 10 \text{ V}, \\ \\ I_C &= 1.0 \text{ MA}, \ V_{CE} = 10 \text{ V}, \\ \\ I_C &= 1.0 \text{ MA}, \ V_{CE} = 10 \text{ V}, \\ \\ I_C &= 1.0 \text{ MA}, \ V_{CE} = 10 \text{ V}, \\ \\ I_C &= 1.0 \text{ MA}, \ V_{CE} = 10 \text{ V}, \\ \\ I_C &= 1.0 \text{ MA}, \ V_{CE} = 10 \text{ V}, \\ \\ I_C &= 1.0 MA$	250	6.5 30 15	pF pF kΩ
SMALL S f _T C _{cb} C _{eb} h _{ie} h _{re}	IGNAL CHARACTERISTICS Current Gain - Bandwidth Product Collector-Base Capacitance Emitter-Base Capacitance Input Impedance Voltage Feedback Ratio	$\begin{split} I_C &= 500 \text{ mA}, \ I_B = 50 \text{ mA} \\ \\ I_C &= 20 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 100 \text{ MHz} \\ \\ V_{CB} &= 5.0 \text{ V}, \ I_E = 0, \\ f &= 140 \text{ kHz} \\ \\ V_{BE} &= 0.5 \text{ V}, \ I_C = 0, \\ f &= 140 \text{ kHz} \\ \\ I_C &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ \\ I_C &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ \end{split}$	250 1.0 0.1	6.5 30 15 8.0	pF pF kΩ x 10 ⁻⁴
SMALL S Ccb Ceb hie hre hoe	IGNAL CHARACTERISTICS Current Gain - Bandwidth Product Collector-Base Capacitance Emitter-Base Capacitance Input Impedance Voltage Feedback Ratio Small-Signal Current Gain	$\begin{split} I_C &= 500 \text{ mA}, \ I_B = 50 \text{ mA} \\ \\ I_C &= 20 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 100 \text{ MHz} \\ \\ V_{CB} &= 5.0 \text{ V}, \ I_E = 0, \\ f &= 140 \text{ kHz} \\ \\ V_{BE} &= 0.5 \text{ V}, \ I_C = 0, \\ f &= 140 \text{ kHz} \\ \\ I_C &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ \\ I_C &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ \\ I_C &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ \\ I_C &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ \\ I_C &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ \\ I_C &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ \\ I_C &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ \\ I_C &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ MA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ MA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ MA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ MA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ MA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ MA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ MA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ MA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ MA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ MA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ MA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ MA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ MA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ MA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ MA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ MA}, \ V_{CE} $	250 1.0 0.1 40	6.5 30 15 8.0 500	pF pF kΩ
SMALL S f _T C _{cb} C _{eb} h _{ie} h _{re} h _{oe} SWITCHI	IGNAL CHARACTERISTICS Current Gain - Bandwidth Product Collector-Base Capacitance Emitter-Base Capacitance Input Impedance Voltage Feedback Ratio Small-Signal Current Gain Output Admittance	$\begin{split} I_C &= 500 \text{ mA}, \ I_B = 50 \text{ mA} \\ \\ I_C &= 20 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 100 \text{ MHz} \\ \\ V_{CB} &= 5.0 \text{ V}, \ I_E = 0, \\ f &= 140 \text{ kHz} \\ \\ V_{BE} &= 0.5 \text{ V}, \ I_C = 0, \\ f &= 140 \text{ kHz} \\ \\ I_C &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ \\ I_C &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ \\ I_C &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ \\ I_C &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ \\ I_C &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ \\ I_C &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ \\ I_C &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ \\ I_C &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ MA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ MA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ MA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ MA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ MA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ MA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ MA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ MA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ MA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ MA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ MA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ MA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ MA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ MA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ MA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ MA}, \ V_{CE} $	250 1.0 0.1 40	6.5 30 15 8.0 500	pF pF kΩ x 10 ⁻⁴
SMALL S f _T C _{cb} C _{eb} h _{ie} h _{re} h _{oe} SWITCHI	IGNAL CHARACTERISTICS Current Gain - Bandwidth Product Collector-Base Capacitance Emitter-Base Capacitance Input Impedance Voltage Feedback Ratio Small-Signal Current Gain Output Admittance	$\begin{split} I_C &= 500 \text{ mA}, \ I_B = 50 \text{ mA} \\ \\ I_C &= 20 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 100 \text{ MHz} \\ \\ V_{CB} &= 5.0 \text{ V}, \ I_E = 0, \\ f &= 140 \text{ kHz} \\ \\ V_{BE} &= 0.5 \text{ V}, \ I_C = 0, \\ f &= 140 \text{ kHz} \\ \\ I_C &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ \\ I_C &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ \\ I_C &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ \\ I_C &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ \\ I_C &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ \\ I_C &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ \\ I_C &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ \\ I_C &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ \\ I_C &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ \\ I_C &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ \\ I_C &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ \\ I_C &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ \\ I_C &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ I_C &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ I_C &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ I_C &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ I_C &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ I_C &= 1.0 \text{ MB}, \ V_$	250 1.0 0.1 40	6.5 30 15 8.0 500	pF pF kΩ x 10 ⁻⁴
SMALL S Ccb Ceb hie hre hoe	IGNAL CHARACTERISTICS Current Gain - Bandwidth Product Collector-Base Capacitance Emitter-Base Capacitance Input Impedance Voltage Feedback Ratio Small-Signal Current Gain Output Admittance NG CHARACTERISTICS Delay Time	$\begin{split} I_C &= 500 \text{ mA}, \ I_B = 50 \text{ mA} \\ \\ I_C &= 20 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 100 \text{ MHz} \\ \\ V_{CB} &= 5.0 \text{ V}, \ I_E = 0, \\ f &= 140 \text{ kHz} \\ \\ V_{BE} &= 0.5 \text{ V}, \ I_C = 0, \\ f &= 140 \text{ kHz} \\ \\ I_C &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ \\ I_C &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ \\ I_C &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ \\ I_C &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ \\ I_C &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ \end{split}$	250 1.0 0.1 40	1.2 6.5 30 15 8.0 500 30	pF pF kΩ x 10 ⁻⁴ μmhos

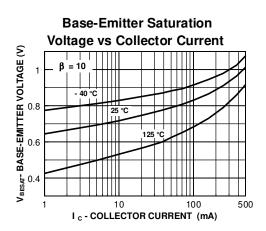
^{*}Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

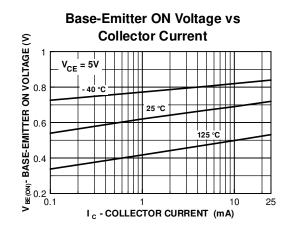
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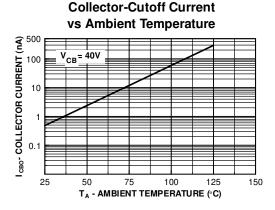
Typical Characteristics

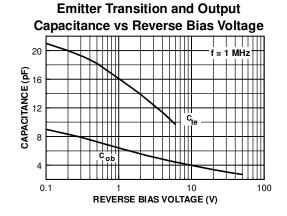








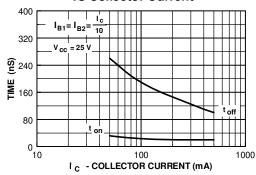




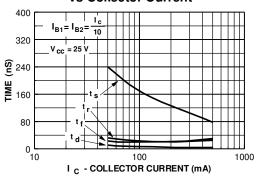
(continued)

Typical Characteristics (continued)

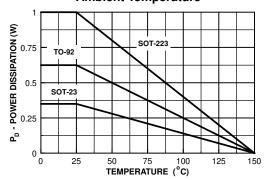
Turn On and Turn Off Times vs Collector Current



Switching Times vs Collector Current

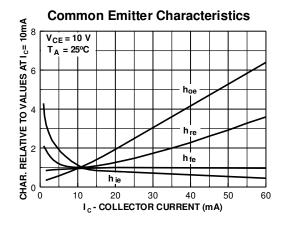


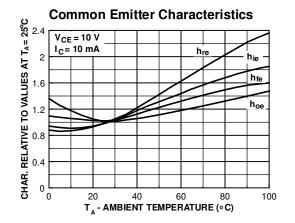
Power Dissipation vs Ambient Temperature

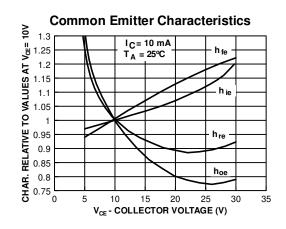


(continued)

Typical Common Emitter Characteristics (f = 1.0kHz)







(continued)

Test Circuits

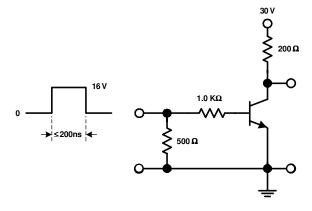


FIGURE 1: Saturated Turn-On Switching Timer

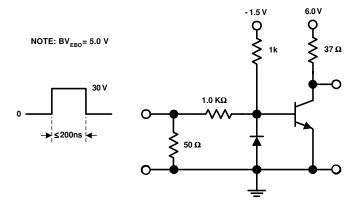


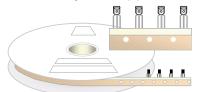
FIGURE 2: Saturated Turn-Off Switching Time

TO-92 Tape and Reel Data FAIRCHILD SEMICONDUCTOR TM **TO-92 Packaging** Configuration: Figure 1.0 **TAPE and REEL OPTION** FSCINT Label sample See Fig 2.0 for various Reeling Styles CBVR/418019 **FSCINT** Label 5 Reels per Intermediate Box Customized F63TNR Label sample Label F63TNR LOT: CBVK741B019 QTY: 2000 FSID: PN222N Customized QTY1: QTY2: 375mm x 267mm x 375mm Intermediate Box TO-92 TNR/AMMO PACKING INFROMATION **AMMO PACK OPTION** See Fig 3.0 for 2 Ammo Packing Style Quantity EOL code **Pack Options** 2,000 D26Z 2,000 Е D27Z Ammo М 2,000 D74Z D75Z 2,000 **FSCINT** $\begin{array}{ll} \mbox{Unit weight} & = 0.22 \mbox{ gm} \\ \mbox{Reel weight with components} & = 1.04 \mbox{ kg} \\ \mbox{Ammo weight with components} & = 1.02 \mbox{ kg} \\ \mbox{Max quantity per intermediate box} & = 10,000 \mbox{ units} \end{array}$ Label 5 Ammo boxes per Intermediate Box 327mm x 158mm x 135mm Immediate Box Customized F63TNR Customized Label Label 333mm x 231mm x 183mm Intermediate Box (TO-92) BULK PACKING INFORMATION **BULK OPTION** See Bulk Packing DESCRIPTION QUANTITY Information table J18Z TO-18 OPTION STD Anti-static Bubble Sheets TO-5 OPTION STD NO LEAD CLIP 1.5 K / BOX J05Z **FSCINT Label** TO-92 STANDARD STRAIGHT FOR: PKG 92, 94 (NON PROELECTRON NO EOL NO LEADCLIP 2.0 K / BOX SERIES), 96 TO-92 STANDARD STRAIGHT FOR: PKG 94 (PROELECTRON SERIES BCXXX, BFXXX, BSRXXX), 97, 98 L34Z NO LEADCLIP 2.0 K / BOX 2000 units per 114mm x 102mm x 51mm EO70 box for std option Immediate Box 5 EO70 boxes per intermediate Box 530mm x 130mm x 83mm Customized Intermediate box Label FSCINT Label 10,000 units maximum per intermediate box for std option

TO-92 Tape and Reel Data, continued

TO-92 Reeling Style Configuration: Figure 2.0

Machine Option "A" (H)

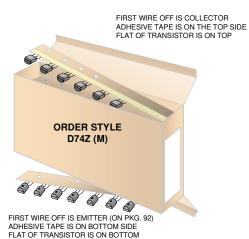


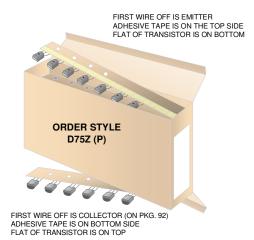
Style "A", D26Z, D70Z (s/h)

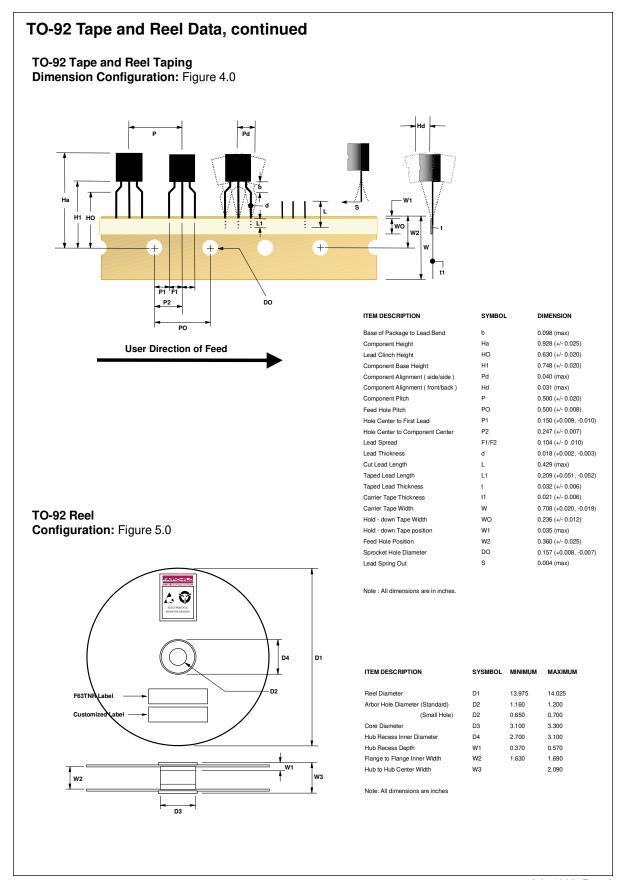
Machine Option "E" (J)

Style "E", D27Z, D71Z (s/h)

TO-92 Radial Ammo Packaging Configuration: Figure 3.0



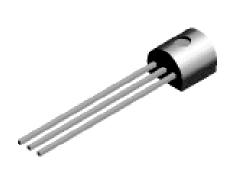


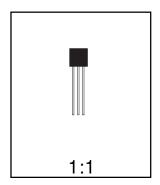


TO-92 Package Dimensions



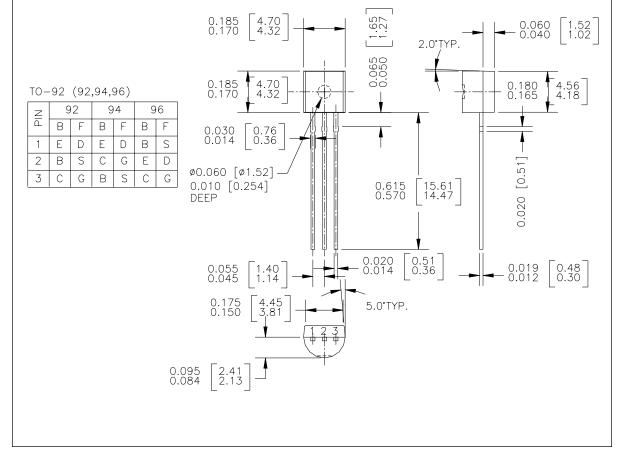
TO-92 (FS PKG Code 92, 94, 96)

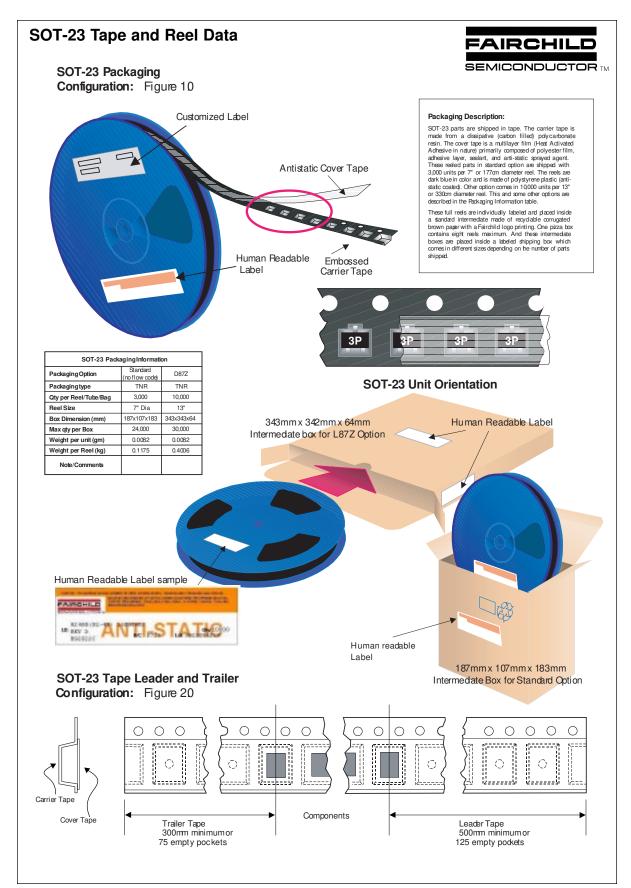




Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.1977

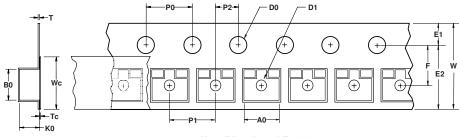




SOT-23 Tape and Reel Data, continued

SOT-23 Embossed Carrier Tape

Configuration: Figure 3.0



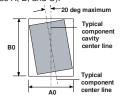
User Direction of Feed

	Dimensions are in millimeter													
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	Т	Wc	Тс
SOT-23 (8mm)	3.15 +/-0.10	2.77 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.30 +/-0.10	0.228 +/-0.013	5.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation

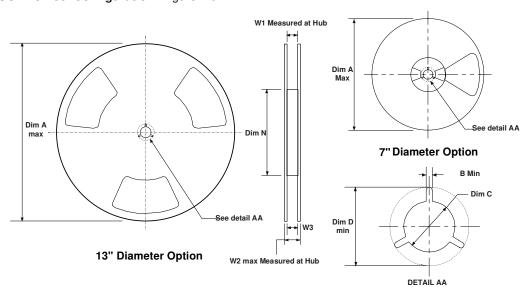


Sketch B (Top View)
Component Rotation



Sketch C (Top View)
Component lateral movement

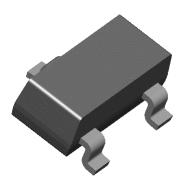
SOT-23 Reel Configuration: Figure 4.0

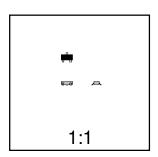


	Dimensions are in inches and millimeters								
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9



SOT-23 (FS PKG Code 49)

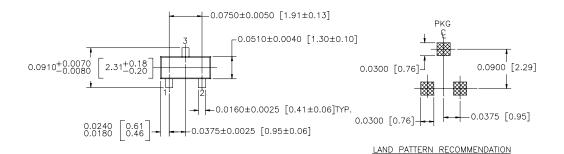


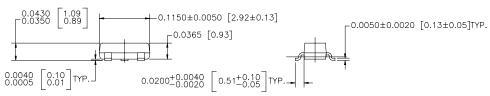


Scale 1:1 on letter size paper

Dimensions shown below are in: inches [millimeters]

Part Weight per unit (gram): 0.0082





CONTROLLING DIMENSION IS INCH VALUES IN [] ARE MILLIMETERS SOT 23, 3 LEADS LOW PROFILE

NOTE: UNLESS OTHERWISE SPECIFIED

- 1. STANDARD LEAD FINISH 150 MICROINCHES / 3.81 MICROMETERS MINIMUM TIN / LEAD (SOLDER) ON ALLOY 42
- 2. REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE G, DATED JUL 1993

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- 2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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